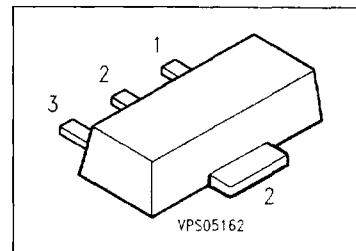


## PNP Silicon AF Transistors

BCX 51 ... BCX 53

### Features

- For AF driver and output stages
- High collector current
- Low collector-emitter saturation voltage
- Complementary types: BCX 54 ... BCX 56 (NPN)



Type	Marking	Ordering Code (tape and reel)	Pin Configuration	Package <sup>1)</sup>		
			1	2	3	
BCX 51	AA	Q62702-C1847	B	C	E	SOT-89
BCX 51-10	AC	Q62702-C1831				
BCX 51-16	AD	Q62702-C1857				
BCX 52	AE	Q62702-C1743				
BCX 52-10	AG	Q62702-C1744				
BCX 52-16	AM	Q62702-C1900				
BCX 53	AH	Q62702-C905				
BCX 53-10	AK	Q62702-C1753				
BCX 53-16	AL	Q62702-C1502				

1) For detailed information see chapter Package Outlines.

**Maximum Ratings**

Parameter	Symbol	Values			Unit
		BCX 51	BCX 52	BCX 53	
Collector-emitter voltage	$V_{CEO}$	45	60	80	V
Collector-base voltage	$V_{CBO}$	45	60	100	
Emitter-base voltage	$V_{EBO}$	5	5	5	
Collector current	$I_C$	1			A
Peak collector current	$I_{CM}$	1.5			
Base current	$I_B$	100			mA
Peak base current	$I_{BM}$	200			
Total power dissipation, $T_S = 130\text{ }^\circ\text{C}$	$P_{tot}$	1			W
Junction temperature	$T_J$	150			$^\circ\text{C}$
Storage temperature range	$T_{stg}$	- 65 ... + 150			

**Thermal Resistance**

Junction - ambient <sup>1)</sup>	$R_{th,JA}$	$\leq 75$	K/W
Junction - soldering point	$R_{th,JS}$	$\leq 20$	

<sup>1)</sup> Package mounted on epoxy pcb 40 mm × 40 mm × 1.5 mm/6 cm<sup>2</sup> Cu.

**Electrical Characteristics**at  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**DC characteristics**

Collector-emitter breakdown voltage $I_C = 10 \text{ mA}$	$V_{(\text{BR})\text{CEO}}$				V
BCX 51		45	—	—	
BCX 52		60	—	—	
BCX 53		80	—	—	
Collector-base breakdown voltage $I_C = 100 \mu\text{A}$	$V_{(\text{BR})\text{CBO}}$				
BCX 51		45	—	—	
BCX 52		60	—	—	
BCX 53		100	—	—	
Emitter-base breakdown voltage $I_E = 10 \mu\text{A}$	$V_{(\text{BR})\text{EBO}}$	5	—	—	
Collector cutoff current $V_{CB} = 30 \text{ V}$	$I_{CBO}$				
$V_{CB} = 30 \text{ V}, T_A = 150^\circ\text{C}$		—	—	100	nA
$V_{CB} = 30 \text{ V}, T_A = 25^\circ\text{C}$		—	—	20	$\mu\text{A}$
Emitter cutoff current $V_{EB} = 4 \text{ V}$	$I_{EBO}$	—	—	20	nA
DC current gain <sup>1)</sup>	$h_{FE}$				—
$I_C = 5 \text{ mA}, V_{CE} = 2 \text{ V}$		25	—	—	
$I_C = 150 \text{ mA}, V_{CE} = 2 \text{ V}$		40	—	250	
BCX 51, BCX 52, BCX 53		63	100	160	
BCX 51-10, BCX 52-10, BCX 53-10		100	160	250	
BCX 51-16, BCX 52-16, BCX 53-16		25	—	—	
$I_C = 500 \text{ mA}, V_{CE} = 2 \text{ V}$		—	—	—	
Collector-emitter saturation voltage <sup>1)</sup>	$V_{CE\text{sat}}$	—	—	0.5	V
$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		—	—	—	
Base-emitter voltage <sup>1)</sup>	$V_{BE}$	—	—	1	
$I_C = 500 \text{ mA}, V_{CE} = 2 \text{ V}$		—	—	—	

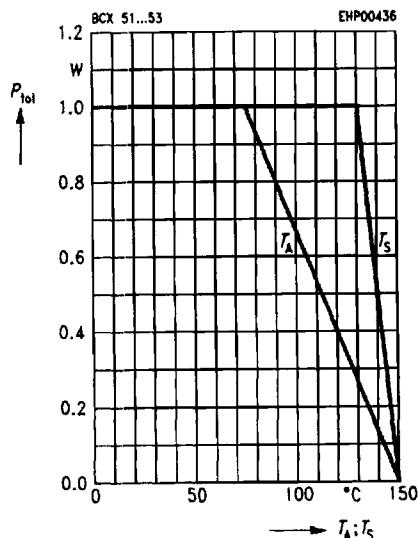
**AC characteristics**

Transition frequency $I_C = 50 \text{ mA}, V_{CE} = 10 \text{ V}, f = 20 \text{ MHz}$	$f$	—	125	—	MHz
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<sup>1)</sup> Pulse test:  $t \leq 300 \mu\text{s}$ ,  $D = 2\%$ .

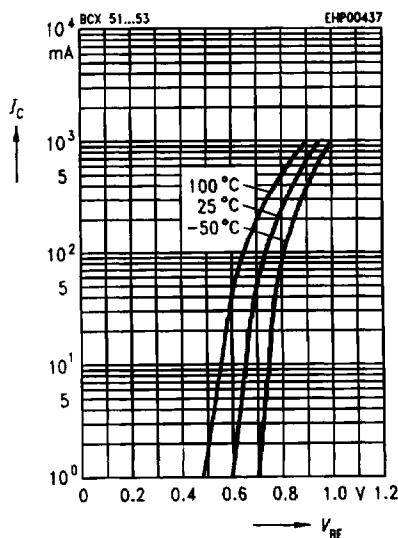
**Total power dissipation**  $P_{\text{tot}} = f(T_A^*; T_S)$

\* Package mounted on epoxy

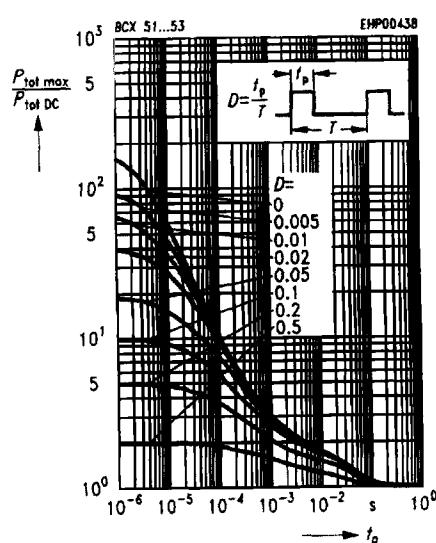


**Collector current**  $I_C = f(V_{BE})$

$V_{CE} = 2 \text{ V}$

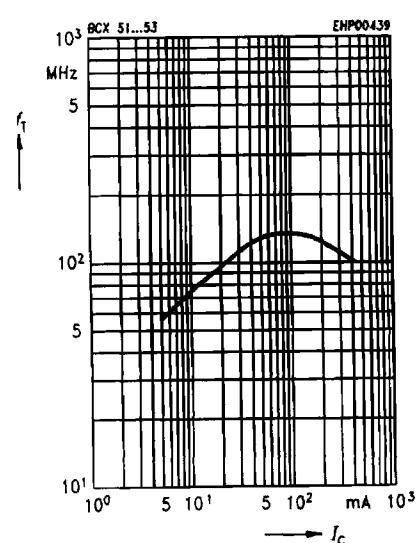


**Permissible pulse load**  $P_{\text{tot max}}/P_{\text{tot DC}} = f(t_p)$



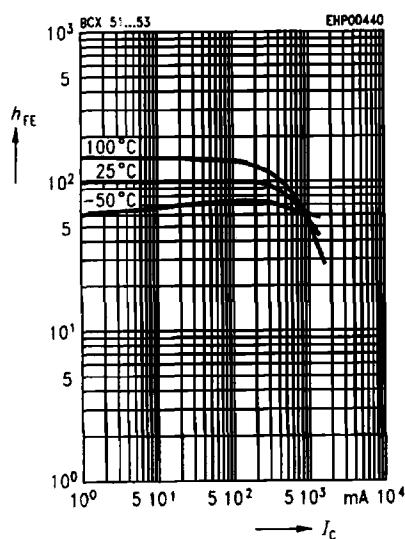
**Transition frequency**  $f_T = f(I_C)$

$V_{CE} = 10 \text{ V}$



**DC current gain**  $h_{FE} = f(I_C)$

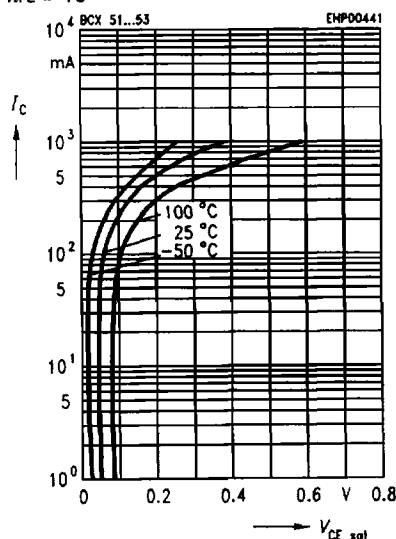
$V_{CE} = 2 \text{ V}$



**Collector-emitter saturation voltage**

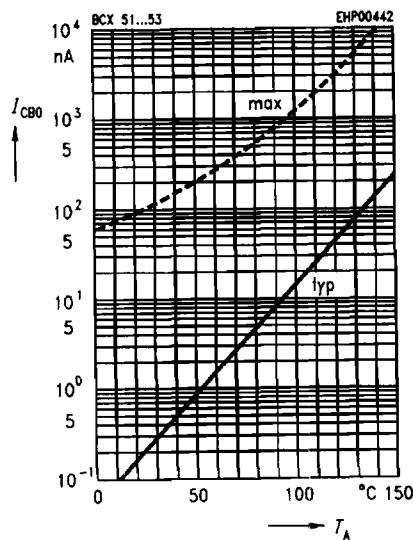
$I_C = f(V_{CE\text{sat}})$

$h_{FE} = 10$



**Collector cutoff current**  $I_{CBO} = f(T_A)$

$V_{CB} = 30 \text{ V}$



**Base-emitter saturation voltage**

$I_C = f(V_{BE\text{sat}})$

$h_{FE} = 10$

